Advanced PECVD-OXIDE				Advanced PECVD SIO2 3000A Typical Film Properties
SiO2 depostion~3000A, T=300C				Deposition rate=27.88nm/min
Step1: OXIDE COAT				Refractive index@632.8nm=1.473
	Name	**Value**	**Changeable**	Stress=-273.21MPa
	Process pressure	800	N	HF etch rate=548.10nm/min
	RF point	30	N	
	stabilization time	15	N	
	step time(m)	**10**	**Y**	
	step time(s)	**0**	**Y**	
	2%SiH4 %He	600	N	
	N2O	1420	N	
Step2: OXIDE DEPOSITION				
	Name	**Value**	**Changeable**	
	Process pressure	800	N	
	RF point	30	N	
	stabilization time	15	N	
	step time(m)	**10**	**Y**	
	step time(s)	**0**	**Y**	
	2%SiH4 %He	600	N	
	N2O	1420	N	
Step3: STANDARD PLASMA CLEAN				
	1. pump down			
	Name	**Value**	**Changeable**	
	stabilization time	15	N	
	step time(m)	0	N	
	step time(s)	30	N	
	2. Pre-purge			
	Name	**Value**	**Changeable**	
	purge=1	1	N	
	stabilization time	15	N	
	step time(m)	**1**	**N**	
	step time(sec)	0	N	
	3.1 High Pressure			
	Name	**Value**	**Changeable**	
	process pressure	600	N	
	RF point=300	300	N	
	stabilization time	35	N	
	step time(m)	30	Y	
	step time(s)	0	Y	
	CF4/O2(5)	500	N	
	4.1 Low pressure			
	Name	**Value**	**Changeable**	
	process pressure	300	N	
	RF setpoint	300	N	
	stabilization time	15	N	
	step time(m)	**30**	**Y**	
	step time(s)	**0**	**Y**	
	CF4/O2(5)	500	N	